Miguel Angel Vidal Borbolla

List of Publications by Year
in descending order

76 papers	1,255 citations	471509 17 h-index	377865 34 g-index
76 all docs	76 docs citations	76 times ranked	1688 citing authors

#	Article	IF	Citations
1	Elastic modulus and hardness of cubic GaN grown by molecular beam epitaxy obtained by nanoindentation. Thin Solid Films, 2020, 699, 137915.	1.8	6
2	Magnetic properties of GaAs:Mn self-assembled nanostructures grown at relatively high-temperature by Molecular Beam Epitaxy. Journal of Magnetism and Magnetic Materials, 2019, 475, 715-720.	2.3	3
3	Effects of Mg incorporation in cubic GaN films grown by PAMBE near Ga rich conditions. Materials Science in Semiconductor Processing, 2019, 93, 196-200.	4.0	8
4	Complex refractive index of InXGa1-XN thin films grown on cubic (100) GaN/MgO. Thin Solid Films, 2017, 626, 55-59.	1.8	6
5	Growth of HfO2/TiO2 nanolaminates by atomic layer deposition and HfO2-TiO2 by atomic partial layer deposition. Journal of Applied Physics, 2017, 121, .	2.5	46
6	Thickness and photocatalytic activity relation in TiO $$_{2}$$ 2 :N films grown by atomic layer deposition with methylene-blue and E. coli bacteria. Bulletin of Materials Science, 2017, 40, 1225-1230.	1.7	1
7	Bending stability of GaN grown on a metallic flexible substrate by plasma-assisted molecular beam epitaxy. Materials Research Express, 2017, 4, 085903.	1.6	1
8	Cubic GaN films grown below the congruent sublimation temperature of (0 0 1) GaAs substrates by plasma-assisted molecular beam epitaxy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, .	1.2	4
9	Structural characterization of AlGaAs:Si/GaAs (631) heterostructures as a function of As pressure. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, 02L119.	1.2	2
10	Effects of growth temperature on the incorporation of nitrogen in GaNAs layers. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, .	1.2	1
11	Tuning emission in violet, blue, green and red in cubic GaN/InGaN/GaN quantum wells. Journal of Crystal Growth, 2016, 435, 110-113.	1.5	10
12	Multiwall carbon nanotubes/polycaprolactone scaffolds seeded with human dental pulp stem cells for bone tissue regeneration. Journal of Materials Science: Materials in Medicine, 2016, 27, 35.	3.6	37
13	Bulk lattice parameter and band gap of cubic InXGa1âˆ’XN (001) alloys on MgO (100) substrates. Journal of Crystal Growth, 2015, 418, 120-125.	1.5	24
14	Determination of the Thermal Expansion Coefficient of Single-Wall Carbon Nanotubes by Raman Spectroscopy. Spectroscopy Letters, 2015, 48, 139-143.	1.0	8
15	Structural and Optical Properties of Ge1-XSnx Alloys Grown on GaAs (001) by R. F. Magnetron Sputtering. ECS Transactions, 2014, 64, 393-400.	0.5	0
16	The effect of the In concentration on the surface morphology of InGaAs-GaAs heterostructures grown by MBE on GaAs substrate. Journal of Physics: Conference Series, 2014, 480, 012038.	0.4	0
17	High-quality InN films on MgO (100) substrates: The key role of 30Â° in-plane rotation. Applied Physics Letters, 2014, 104, 191904.	3.3	2
18	Functionalization of nitrogen-doped carbon nanotubes with gallium to form Ga-CN_x-multi-wall carbon nanotube hybrid materials. Nanotechnology, 2012, 23, 325601.	2.6	9

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19	Self-Assembly of Î²GaN/MgO Nanobars. Advanced Science Letters, 2012, 16, 229-236.	0.2	0
20	High-Sensitivity Bolometers from Self-Oriented Single-Walled Carbon Nanotube Composites. ACS Applied Materials & Interfaces, 2011, 3, 3200-3204.	8.0	46
21	Effect of hydrogen concentration on the bolometric performance of sputtered a-SixGe1â^'x:H films. Thin Solid Films, 2011, 519, 6522-6524.	1.8	1
22	Photoluminescence and secondary ion mass spectrometry study of layer-by-layer grown Zn1â^'xCdxSe quantum wells. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 03C137.	1.2	3
23	Liquid crystal behavior of single wall carbon nanotubes. Carbon, 2010, 48, 3531-3542.	10.3	35
24	Infrared study of the absorption edge of Î²-InN films grown on GaN/MgO structures. Journal of Applied Physics, 2010, 108, .	2.5	4
25	Critical thickness of Î²-InN/GaN/MgO structures. Journal of Applied Physics, 2010, 107, 083510.	2.5	11
26	Infrared reflectance anisotropy of wurzite GaN. Journal of Applied Physics, 2009, 106, 063523.	2.5	0
27	In situ measurements of the critical thickness for strain relaxation in Î²-GaN/MgO structures. Journal of Crystal Growth, 2009, 311, 1302-1305.	1.5	8
28	Low energy shifted photoluminescence of Er3+ incorporated in amorphous hydrogenated siliconâ€“germanium alloys. Journal of Non-Crystalline Solids, 2009, 355, 976-981.	3.1	1
29	On the doping problem of CdTe films: The bismuth case. Thin Solid Films, 2008, 516, 7013-7015.	1.8	5
30	Controlling the dimensions, reactivity and crystallinity of multiwalled carbon nanotubes using low ethanol concentrations. Chemical Physics Letters, 2008, 453, 55-61.	2.6	66
31	Nonlinear behavior of the energy gap in Ge1â^'xSnx alloys at 4K. Applied Physics Letters, 2007, 91, .	3.3	43
32	AFM and FTIR characterization of microcrystalline Si obtained from isothermal annealing of Al/a-Si:H. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 1014-1017.	1.8	1
33	Characterization of Sputtered Ge-Sn Thin Films by High Resolution Methods. Microscopy and Microanalysis, 2006, 12, 712-713.	0.4	2
34	In-plane and out-of-plane lattice parameters of [11n] epitaxial strained layers. Journal of Crystal Growth, 2006, 291, 340-347.	1.5	10
35	Structural and optical characterization of GaNAs layers grown by molecular beam epitaxy. Journal of Vacuum Science & Technology B, 2006, 24, 1591.	1.3	5
36	Determination of the optical energy gap of Ge1â^'xSnx alloys with 0<x<0.14. Applied Physics Letters, 2004, 84, 4532-4534.	3.3	83

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37	Effect of structural imperfections on luminescence of ZnCdSe/ZnSe quantum wells. Journal of Alloys and Compounds, 2004, 371, 202-205.	5.5	0
38	Study of the optical and structural properties of GaN films grown on Si substrates with a SiC layer. Thin Solid Films, 2003, 433, 68-72.	1.8	6
39	Raman studies of aluminum induced microcrystallization of n+ Si:H films produced by PECVD. Thin Solid Films, 2003, 445, 32-37.	1.8	5
40	Characterization of GaAs grown by the close-spaced vapor transport technique, using atomic hydrogen as the reactant. Physica Status Solidi A, 2003, 198, 289-296.	1.7	1
41	An interface clusters mixture model for the structure of amorphous silicon monoxide (SiO). Journal of Non-Crystalline Solids, 2003, 320, 255-280.	3.1	231
42	Ge1â^'xSnx alloys pseudomorphically grown on Ge(001). Applied Physics Letters, 2003, 83, 4942-4944.	3.3	45
43	Structural study of ZnSe films grown on substrate with InxGa1-xAs and Al1-xGaxAs buffer layers: strain, relaxation and lattice parameter. Journal Physics D: Applied Physics, 2002, 35, 1408-1413.	2.8	5
44	Structural characterization of semi-strained layer (GaAs)1â^'x(Si2)x/GaAs multilayers grown by magnetron sputtering. Thin Solid Films, 2002, 416, 49-53.	1.8	0
45	Study of the crystal quality and Ga-segregation in ZnSe films grown by molecular beam epitaxy on AlxGa1â^'xAs and InxGa1â^'xAs buffer layers on GaAs substrates. Journal of Crystal Growth, 2001, 227-228, 639-644.	1.5	3
46	STUDY OF STOICHIOMETRIC AND NON-STOICHIOMETRIC CADMIUM SELENIDE THIN FILMS. Modern Physics Letters B, 2001, 15, 741-744.	1.9	7
47	Raman study of luminescent spark processed porous GaAs. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 622.	1.6	8
48	Effects of the substrate tilting angle on the molecular beam epitaxial growth of GaAs on Si(110). Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 1567.	1.6	3
49	Growth of strained-layer GaAs/Ge superlattices by magnetron sputtering: Optical and structural characterization. Journal of Applied Physics, 2001, 89, 3209-3214.	2.5	4
50	Raman scattering study of (GaAs)1â^'x(Si2)x alloys epitaxially grown on GaAs. Journal of Applied Physics, 2001, 90, 4977-4980.	2.5	6
51	Physical properties of(GaAs)1â^'x(Ge2)x:â€ƒInfluence of growth direction. Physical Review B, 2001, 63, .	3.2	11
52	Long-range orderâ€“disorder transition in (GaAs)1â^'(Ge2) grown on GaAs(001) and GaAs(111). Microelectronics Journal, 2000, 31, 439-441.	2.0	5
53	Characterization of ZnSe films grown on GaAs substrates with InxGaâ^'xAs and AlxGa1â^'xAs buffer layers. Thin Solid Films, 2000, 373, 37-40.	1.8	3
54	Raman scattering study of photoluminescent spark-processed porous InP. Thin Solid Films, 2000, 379, 1-6.	1.8	44

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55	Influence of growth direction on orderâ€“disorder transition in (GaAs)1âˆ’x(Ge)2x semiconductor alloys. Applied Physics Letters, 2000, 77, 2497-2499.	3.3	10
56	Dependence on the atmosphere of preparation of the luminescence of spark processed porous GaAs. Journal of Applied Physics, 2000, 87, 1270-1275.	2.5	10
57	Processing of porous GaAs at low frequency sparking. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1999, 17, 624-629.	2.1	6
58	Observation of zinc-blende to diamond transition in metastable (GaAs)1âˆ’x(Ge2)x alloys by Raman scattering. Solid State Communications, 1999, 109, 295-300.	1.9	14
59	Epitaxial Growth of Strained Ge Films on GaAs(001). Thin Solid Films, 1999, 352, 269-272.	1.8	15
60	Stress in GaAs at the hetero-interface of ZnSe/GaAs/GaAs: a possible effect of pit filling and difference in thermal expansion coefficients. Applied Surface Science, 1999, 151, 271-279.	6.1	6
61	Structural study of metastable (GaAs)1âˆ’X(Ge2)X thin films grown by RF magnetron sputtering. Journal of Crystal Growth, 1999, 197, 783-788.	1.5	8
62	Near band-edge optical properties of GaAs at interfaces of ZnSe/GaAs/GaAs by phase selection in photoreflectance. Journal of Applied Physics, 1999, 86, 425-429.	2.5	5
63	Model for the linear electro-optic reflectance-difference spectrum of GaAs(001) aroundE1andE1+Î”1. Physical Review B, 1999, 59, 10234-10239.	3.2	49
64	Dislocation densities in MBE grown ZnSe epitaxial layers on GaAs by HRXRD. Journal of Crystal Growth, 1998, 194, 301-308.	1.5	13
65	Luminescence of spark processed porous InP. Thin Solid Films, 1998, 322, 282-289.	1.8	4
66	Influence of ion sputtering on the surface topography of GaAs. Applied Surface Science, 1998, 126, 205-212.	6.1	3
67	Observation of stress effects on GaAs at the interface of molecular beam epitaxy grown ZnSe/GaAs(100) heterostructures. Applied Surface Science, 1998, 134, 95-102.	6.1	5
68	Optical and structural characterization of ZnSe films grown by molecular beam epitaxy on GaAs substrates with and without GaAs buffer layers. Journal of Applied Physics, 1998, 84, 1551-1557.	2.5	20
69	Excitonic transitions in (GaAs)1âˆ’x(Ge2)x/GaAs multilayers grown by magnetron sputtering. Applied Physics Letters, 1998, 72, 94-96.	3.3	4
70	Electron spin resonance on a two-dimensional electron gas. Physical Review B, 1997, 56, R4359-R4362.	3.2	34
71	Optical characterization of vacuum evaporated cadmium sulfide films. Thin Solid Films, 1997, 305, 345-350.	1.8	92
72	Temperature dependence of the band gap of Cd1âˆ’xZnxTe alloys of low zinc concentrations. Journal of Applied Physics, 1996, 79, 7713-7717.	2.5	31

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73	Refractive indices of zincblende structure Î²â€GaN(001) in the subbandâ€gap region (0.7â€“3.3 eV). Applied Physics Letters, 1996, 68, 441-443.	3.3	22
74	Monte Carlo simulation of the transport process in the growth ofaâ€Si:H prepared by cathodic reactive sputtering. Journal of Applied Physics, 1990, 67, 477-482.	2.5	17
75	Hydrogen detection in hydrogenated amorphous silicon by ionâ€induced Auger spectroscopy. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1989, 7, 2625-2627.	2.1	0
76	Thermal annealing effects on amorphous radio frequency sputtered Cd0.95Fe0.05Te thin films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1987, 5, 1798-1801.	2.1	8